

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently amended) A method for forming a stratum consisting of semiconductor particles, comprising the steps of:

a) forming an original plurality of discrete semiconductor particles from one of a source of semiconductor material and a precursor for said semiconductor material, said original plurality of discrete semiconductor particles entrained in a gas and thereby forming an aerosol, substantially all of said original plurality of discrete semiconductor particles having a diameter less than 20 nanometers;

b) densifying said original plurality of discrete semiconductor particles by heating said aerosol in a substantially oxygen-free environment to a sufficiently high temperature [~~to densify said particles~~] such that substantially all of said particles include a density substantially as great as the bulk density of said semiconductor material and thereby forming a corresponding plurality of densified discrete semiconductor particles entrained in a gas;

c) forming an electrically insulating cover on each of said plurality of densified discrete semiconductor particles, thereby forming a corresponding plurality of insulator-coated densified discrete semiconductor particles; and

d) depositing said plurality of insulator-coated densified discrete semiconductor particles on a substrate thereby forming a stratum of discrete, electrically isolated semiconductor particles on said substrate.

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2. (Original) The method as in claim 1, in which step a) includes pyrolyzing a gas.

3. (Original) The method as in claim 2, in which step a) includes said pyrolyzing occurring during a ramp-up period ranging from 10-50 msec, during which said gas is heated to a maximum temperature.

4. (Original) The method as in claim 3, in which said maximum temperature lies within the range of 950°C to 1150°C.

5. (Original) The method as in claim 3, in which said gas flows through a pyrolysis furnace at a flow rate ranging from 650 to 850 sccm during said ramp-up period.

6. (Original) The method as in claim 3, in which step a) includes intermixing said gas with a diluent gas prior to said gas attaining said maximum temperature.

7. (Original) The method as in claim 3, further comprising maintaining said gas at said maximum temperature during said step of heating for a time ranging from 200 msec to 600 msec.

8. (Currently Amended) The method as in claim 1, further comprising ~~in which said step b) includes said~~ heating to convert ~~[converting]~~ a majority of said original plurality of discrete semiconductor particles to single crystalline material, said heating occurring at a sintering temperature within the range of 950°C to 1150°C.

9. (Currently Amended) The method as in claim 1[8], in which step a) includes pyrolyzing ~~[pyrolyzing]~~ a gas during a ramp-up period ranging from 10-50 msec,

during which said gas is heated to ~~said~~ a sintering temperature within the range of 950°C to 1150°C and intermixed with a diluent gas to form a gas mixture, and said step b) includes said gas mixture having a flow rate ranging from 1300 sccm to 1700 sccm.

10. (Original) The method as in claim 1, in which step c) comprises thermal oxidation and said cover comprises an oxide cover.

11. (Cancelled)

12. (Original) The method as in claim 1, in which step c) includes reacting surfaces of said particles with a gas.

13. (Cancelled)

14. (Cancelled)

15. (Original) The method as in claim 1, in which said original plurality of discrete semiconductor particles comprise silicon particles and said insulator-coated densified discrete semiconductor particles each include a silicon core and a silicon dioxide shell.

16. (Original) The method as in claim 2, in which said step a) includes delivering said gas to a pyrolysis furnace in the form of a gas stream, said gas stream including a mixture of a carrier gas having a flow rate within the range of 650 sccm to 850 sccm, and silane gas and including about 5000 ppm of silane in nitrogen and having a flow rate less than 1 sccm.

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17. (Original) The method as in claim 2, in which said gas includes silane and a carrier species, and said step a) includes delivering said gas and a diluent gas to a pyrolysis furnace.

18. (Original) The method as in claim 17, in which said diluent gas comprises nitrogen.

19. (Original) The method as in claim 17, in which said gas is delivered within a tube axially disposed within a further tube, said diluent gas is delivered within said further tube, and said gas and said diluent gas are allowed to intermix within said pyrolysis furnace.

20. (Currently amended) The method as in claim 1, further comprising the step of classifying particles of said plurality of densified discrete semiconductor particles after step b), and directing said [~~a-classified~~] plurality of densified discrete semiconductor particles, classified within a pre-selected range of sizes, for further processing.

21. (Original) The method as in claim 20, in which said pre-selected range of sizes includes particles having average diameters within the range of 5-10 nm.

22. (Original) The method as in claim 20, in which said step of classifying includes applying an electric field to a differential mobility analyzer.

23. (Original) The method as in claim 20, in which said step of classifying includes time-of-flight separation of a focused particle beam.

24. (Original) The method as in claim 20, further comprising cooling said discrete semiconductor particles after said step of heating and prior to said step of classifying.

25. (Original) The method as in claim 1, in which step d) comprises delivering said plurality of insulator-coated densified discrete semiconductor particles to a deposition chamber including said substrate therein, and thermophoretically depositing said plurality of insulator-coated densified discrete semiconductor particles on said substrate.

26. (Original) The method as in claim 25, in which step d) includes maintaining said substrate at a temperature which is at least 175°C cooler than internal portions of said deposition chamber.

27. (Original) The method as in claim 1, in which step d) includes thermophoretically depositing said stratum to include a density of  $10^{12}$ - $10^{13}$  particles/cm<sup>2</sup>.

28. (Original) The method as in claim 1, in which step d) produces said stratum which is characterized by a foreign contamination level being less than  $10^{11}$  atoms/cm<sup>2</sup>.

29. (Original) The method as in claim 1, in which said substrate includes a dielectric layer formed thereon and said step d) comprises depositing said insulator-coated densified discrete semiconductor particles on said dielectric layer, thereby forming said stratum over said dielectric layer.

30. (Original) The method as in claim 29, in which said dielectric layer comprises a tunnel oxide and further comprising the steps of:

forming a gate dielectric film over said stratum;  
forming a gate electrode over said gate dielectric film; and  
defining a gate region and removing portions of said gate electrode, said gate dielectric film, said stratum, and said tunnel oxide from regions outside of said gate region.

31. (Original) The method as in claim 30, in which said tunnel oxide includes a thickness within the range of 3 to 12 nanometers.

32. (Original) The method as in claim 1, in which step d) includes said stratum being essentially a monolayer of said oxidized semiconductor particles.

33. (Original) The method as in claim 1, in which step d) includes:  
introducing said plurality of insulator-coated densified discrete semiconductor particles into a liquid medium to form a colloid; and  
electrophoretically depositing said plurality of insulator-coated densified discrete semiconductor particles onto a surface of said substrate.

34. (Original) The method as in claim 1, in which step d) includes:  
delivering said plurality of insulator-coated densified discrete semiconductor particles to a deposition chamber which includes said substrate therein; and  
forming an ordered structure of said plurality of insulator-coated densified discrete semiconductor particles on said substrate, using contact mode atomic force microscopy.

35. (Original) The method as in claim 34, in which said step d) comprises forming a wire of said insulator-coated densified discrete semiconductor particles.

36. (Cancelled)

37. (Cancelled)

38. (Cancelled)

39. (Cancelled)

40. (Original) A method for forming a stratum consisting of semiconductor particles, comprising the steps of:

pyrolyzing a particle source gas to produce an original plurality of discrete semiconductor particles;

quenching said particle source gas with a diluent gas during said step of pyrolyzing;

classifying particles of said original plurality of discrete semiconductor nanoparticles by size and directing a classified plurality of said discrete semiconductor particles to a deposition chamber which includes a substrate therein; and

thermophoretically depositing said classified plurality of said discrete semiconductor particles on said substrate thereby forming a discontinuous layer of said discrete semiconductor particles on said substrate.

41. (Original) The method as in claim 40, further comprising the step of sintering said original plurality of discrete semiconductor particles to form a corresponding plurality of crystalline semiconductor particles.

42. (Original) The method as in claim 1, wherein said step c) comprises encapsulating said particles.

43. (Cancelled)

44. (Cancelled)

45. (New) A method for forming a stratum consisting of semiconductor particles, comprising the steps of:

forming an original plurality of discrete semiconductor particles from one of a source of semiconductor material and a precursor for said semiconductor material, said original plurality of discrete semiconductor particles entrained in a gas and thereby forming an aerosol, substantially all of said original plurality of discrete semiconductor particles having a diameter less than 20 nanometers;

densifying said original plurality of discrete semiconductor particles by heating said aerosol in a substantially oxygen-free environment to a sufficiently high temperature for a time ranging from 200 to 600 milliseconds such that substantially all of said particles include a density substantially as great as the bulk density of said semiconductor material and thereby forming a corresponding plurality of densified discrete semiconductor particles entrained in a gas;

forming an electrically insulating cover on each of said plurality of densified discrete semiconductor particles, thereby forming a corresponding plurality of insulator-coated densified discrete semiconductor particles; and

delivering said plurality of insulator-coated densified discrete semiconductor particles to a deposition chamber including a substrate therein, and thermophoretically depositing said plurality of insulator-coated densified discrete semiconductor particles on said substrate.